Short CV

Name	**Charalabos Dimitriadis**
Position	Professor
Studies	-B.S. Physics, Aristotle University of Thessaloniki, Greece, April 1974. -M.S. Solid State Electronics, Electrical Engineering, University of Manchester Institute of Science and Technology (UMIST), England, December 1976. -Ph.D. Solid State Electronics, Electrical Engineering, University of Manchester Institute of Science and Technology (UMIST), England, July 1979.
Scientific expertise	- Physics and technology of semiconductor devices - Low frequency noise of semiconductor devices - Reliability of semiconductor devices
Research activities	- Polysilicon and transparent oxide TFTs, - Analytical compact modelling of nano-scale multi-gate MOSFET and ultra-thin body ultra-thin BOX FDSOI devices. - Manufacturing variability modelling of nanoscale MOSFETs. - Low frequency noise modelling of nano-scale multi-gate MOSFETs, FD-SOI and bulk MOSFETs. - Static and dynamic low-frequency and radio telegraph noise variability modelling of nanoscale MOSFETs. - Numerical simulation of nanoscale multi-gate MOSFETs.
Five most important publications	- E.G. Ioannidis, S. Haendler, A. Pahron, N. Planes, F. Arnaud, R.A. Bianchi, M. Haond, D. Golanski, J. Rosa, C. Fenouillet-Beranger, P. Perreau, C.A. Dimitriadis, G. Ghibaudo, Low frequency noise variability in high-k/metal gate stack 28nm bulk and FD-SOI CMOS transistors, IEDM 2011, Washington, USA. - A. Tsormpatzoglou, N.A. Hastas, S. Khan, C.A. Dimitriadis, and M. Hatalis, Comparative study of active-over-metal and metal-over-active amorphous IGZO thin-film transistors with low frequency noise measurements, IEEE Electron Dev. Lett. 33, p. 555 (2012). - N. Fasarakis, A. Tsormpatzoglou, D.H. Tassis, I. Pappas, K. Papathanasiou, M. Bucher, G. Ghibaudo, and C.A. Dimitriadis, Compact model of drain current in short-channel triple-gate FinFETs, IEEE Trans. Electron Dev. 59, 1891 (2012). - E.G. Ioannidis, C.A. Dimitriadis, S. Haendler, R.A. Bianchi, J. Jomaah, and G. Ghibaudo, Improved naalysis and modeling of low-frequency noise in nanoscale MOSFETs Solid State Electron. 76, 54 (2012). - N. Fasarakis, A. Tsormpatzoglou, D.H. Tassis, I. Pappas, K. Papathanasiou, M. Bucher, G. Ghibaudo, and C.A. Dimitriadis, Compact capacitance model of undoped or lightly-doped ultra-scaled triple-gate FinFETs, IEEE Trans. Electron Dev. 59, 3306 (2012).